Vishay Semiconductors

Fast Recovery Diodes (T-Modules), 40 A, 70 A, 85 A



D-55 (T-module)

PRIMARY CHARACTERISTICS						
I _{F(AV)}	40 A, 70 A, 85 A					
Type	Modules - diode, fast					
V _{RRM}	100 V to 1000 V					
Package	D-55 (T-module)					
Circuit configuration	Single					

FEATURES

- Fast recovery time characteristics
- · Electrically isolated base plate
- 3500 V_{RMS} isolating voltage
- Standard JEDEC® package
- Simplified mechanical designs, rapid assembly
- Large creepage distances
- UL E78996 approved
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The series of T-modules uses fast recovery power diodes in a single diode configuration. The semiconductors are electrically isolated from the metal base, allowing common heatsink and compact assemblies to be built.

These single diode modules can be used in conjunction with the thyristor modules as a freewheel diode. Application includes self-commutated inverters, DC choppers, motor control, inductive heating and electronic welders. These modules are intended for those applications where very fast recovery characteristics are required and for general power switching applications.

MAJOR R	MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS		UNITS					
STMBOL	CHARACTERISTICS	T40HFL	T70HFL	T85HFL	UNITS			
1		40	70	85	Α			
I _{F(AV)}	T _C	70	70	70	°C			
I _{F(RMS)}		63	110	133	A			
1	50 Hz	475	830	1300	Δ.			
I _{FSM}	60 Hz	500	870	1370	_ A			
l ² t	50 Hz	1130	3460	8550	A ² s			
1-1	60 Hz	1030	3160	7810	A-S			
V _{RRM}	Range		V					
t _{rr}	Range	200 to 1000 ns						
TJ	Range	-40 to +125 °C						

ELECTRICAL SPECIFICATIONS

VOLTAGE F	RATINGS				
TYPE NUMBER	VOLTAGE CODE	t _{rr} CODE	V _{RRM,} MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 25 °C μΑ
	10	S02, S05, S10	100	150	
	20	S02, S05, S10	200	300	
VS_T40HFL VS_T70HFL	40	S02, S05, S10	400	500	100
VS_T85HFL	60	S02, S05, S10	600	700	100
_	80	S05, S10	800	900	
	100	S05, S10	1000	1100	



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FORWARD CONDUCTION									
PARAMETER	SYMBOL	CVMPOL TEST COMPLTIONS			VALUES			LINUTO	
PARAMETER	STIVIBUL		TEST CONDITIONS		T40HFL	T70HFL	T85HFL	UNITS	
Maximum average forward current at case temperature	I _{F(AV)}	180° condu	uction, half sine	e wave	40	70 70	85	A °C	
Maximum RMS forward current	I _{F(RMS)}				63	110	133	Α	
	. ()	t = 10 ms	No voltage		475	830	1300		
Maximum pools and avalatement		t = 8.3 ms	reapplied		500	870	1370		
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	100 %		400	700	1100	Α	
		t = 8.3 ms	V _{RRM} reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	420	730	1150		
	l ² t	t = 10 ms	No voltage		1130	3460	8550		
		t = 8.3 ms	reapplied		1030	3160	7810		
Maximum I ² t for fusing		t = 10 ms	100 %		800	2450	6050	A ² s	
		t = 8.3 ms	V _{RRM} reapplied		730	2230	5520		
Maximum I ² √t for fusing	l²√t	t = 0.1 ms	to 10 ms, no v	oltage reapplied	11 300	34 600	85 500	A²√s	
Low level value of threshold voltage	V _{F(TO)1}	T _J = 25 °C,	, (16.7 % x π x	$I_{F(AV)} < I < \pi \times I_{F(AV)}$	0.82	0.87	0.84		
High level value of threshold voltage	V _{F(TO)2}	T _J = 25 °C,	$T_{J} = 25 ^{\circ}\text{C}, (I > \pi \times I_{F(AV)})$			0.90	0.86	V	
Low level value of forward slope resistance	r _{f1}	$T_J = 25 \text{ °C}, (16.7 \% \text{ x } \pi \text{ x } I_{F(AV)} < I < \pi \text{ x } I_{F(AV)})$			7.0	2.77	2.15	0	
High level value of forward slope resistance	r _{f2}	$T_{J} = 25 {}^{\circ}\text{C}, (I > \pi \times I_{F(AV)})$			6.8	2.67	2.07	mΩ	
Maximum forward voltage drop	V_{FM}			, $t_p = 400 \mu s$ square wave $I_{F(AV)} + r_f x (I_{F(RMS)})^2$	1.60	1.73	1.55	V	

REVERSE RE	REVERSE RECOVERY CHARACTERISTICS											
PARAMETER	SYMBOL	TEST CONDITIONS (1)	T40HFL			T70HFL			T85HFL			UNITS
PANAMETEN	STIVIBUL	TEST CONDITIONS (7	S02	S05	S10	S02	S05	S10	S02	S05	S10	UNITS
Maximum reverse	+	$T_J = 25 ^{\circ}\text{C}$, $-dI_F/dt = 100 \text{A/}\mu\text{s}$ $I_F = 1 \text{A to V}_R = 30 \text{V}$	70	110	270	70	110	270	80	120	290	ne
recovery time t _{rr}	$T_J = 25$ °C, $-dI_F/dt = 25$ A/ μ s $I_{FM} = \pi$ x rated $I_{F(AV)}$, $V_R = -30$ V	200	500	1000	200	500	1000	200	500	1000	ns	
Maximum reverse		$T_J = 25 ^{\circ}\text{C}$, $-dI_F/dt = 100 \text{A/}\mu\text{s}$ $I_F = 1 \text{A to V}_R = 30 \text{V}$	0.25	0.4	1.35	0.25	0.4	1.35	0.3	0.6	1.6	
recovery charge Q _{rr}	$T_J = 25$ °C, $-dI_F/dt = 25$ A/ μ s $I_{FM} = \pi x$ rated $I_{F(AV)}$, $V_R = -30$ V	0.55	2.0	8.0	0.6	2.1	8.5	0.8	3.5	1.5	μC	

Note

⁽¹⁾ Tested on LEM 300 A diodemeter tester

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	T40HFL	T70HFL	T85HFL	UNITS
Maximum peak reverse leakage current	I _{RRM}	T _J = 125 °C		20		mA
RMS isolation voltage	V _{ISOL}	50 Hz, circuit to base, all terminals shorted, $T_J = 25^{\circ}\text{C}$, $t = 1\text{s}$		3500		V

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PARAMETER		SYMBOL	TE	ST CONDITIONS	VALUES	UNITS	
Junction operating temperatur	re range	TJ			-40 to +125	°C	
Storage temperature range		T _{Stg}			-40 to +150		
Maximum internal thermal	T40HFL				0.85		
resistance, junction to case per module	T70HFL	R_{thJC}		DC operation	0.53	K/W	
	T85HFL	1			0.46	1	
Thermal resistance, case to heatsink per module		R _{thCS}		Mounting surface, flat, smooth and greased	0.2		
Mounting torque : 10.0/	base to heatsink		Non-lubricated	M3.5 mounting screws (1)	1.3 ± 10 %	Nima	
Mounting torque ± 10 %	busbar to terminal		threads	M5 screws terminals	3 ± 10 %	Nm	
Approximate weight				See dimensions -	54	g	
Approximate weight				link at the end of datasheet	19	OZ.	
Case style					D-55 (T-mo	dule)	

Note

⁽¹⁾ A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound

△R CONDUCTION											
DEVICES	SINUS	OIDAL CO	NDUCTION	AT T _J MA	XIMUM	RECTAN	GULAR C	ONDUCTIO	N AT T _J M	AXIMUM	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
T40HFL	0.06	0.08	0.10	0.14	0.24	0.05	0.08	0.10	0.15	0.24	
T70HFL	0.05	0.06	0.08	0.11	0.19	0.04	0.06	0.08	0.12	0.19	K/W
T85HFL	0.04	0.05	0.06	0.09	0.15	0.03	0.05	0.07	0.09	0.015	

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

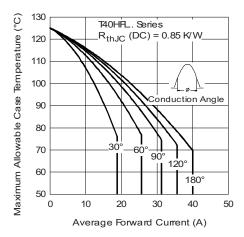


Fig. 1 - Current Ratings Characteristics

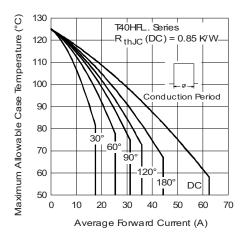


Fig. 2 - Current Ratings Characteristics

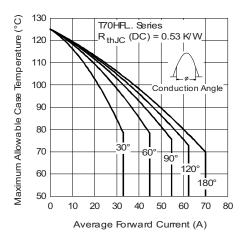


Fig. 3 - Current Ratings Characteristics

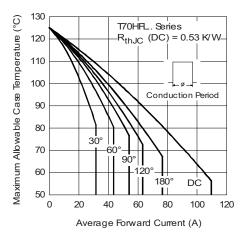


Fig. 4 - Current Ratings Characteristics

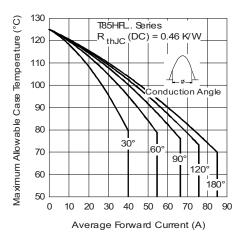


Fig. 5 - Current Ratings Characteristics

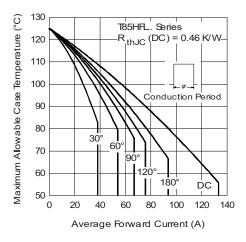


Fig. 6 - Current Ratings Characteristics

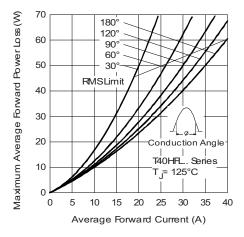


Fig. 7 - Forward Power Loss Characteristics

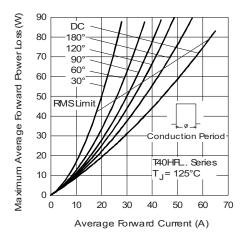


Fig. 8 - Forward Power Loss Characteristics

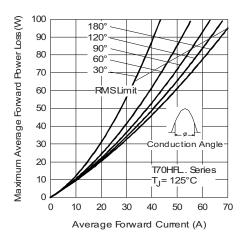


Fig. 9 - Forward Power Loss Characteristics

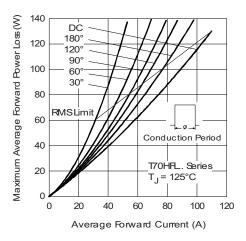


Fig. 10 - Forward Power Loss Characteristics

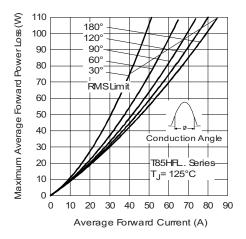


Fig. 11 - Forward Power Loss Characteristics

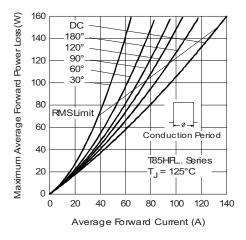


Fig. 12 - Forward Power Loss Characteristics

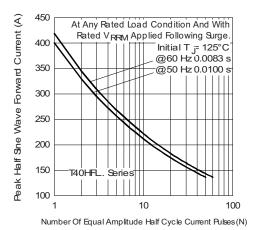


Fig. 13 - Maximum Non-Repetitive Surge Current

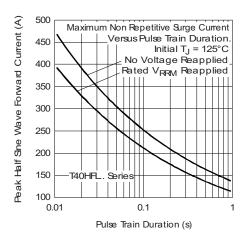


Fig. 14 - Maximum Non-Repetitive Surge Current

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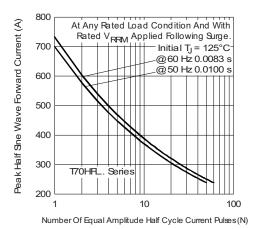


Fig. 15 - Maximum Non-Repetitive Surge Current

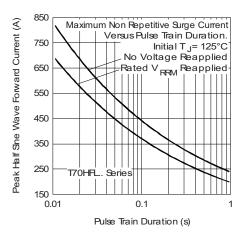


Fig. 16 - Maximum Non-Repetitive Surge Current

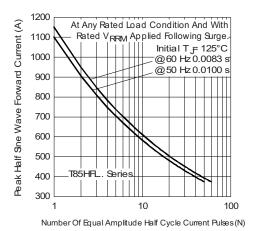


Fig. 17 - Maximum Non-Repetitive Surge Current

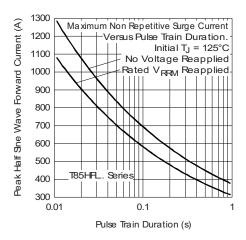
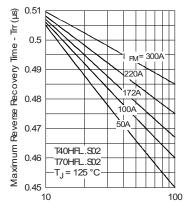
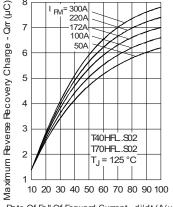


Fig. 18 - Maximum Non-Repetitive Surge Current



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 19 - Recovery Time Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 20 - Recovery Charge Characteristics

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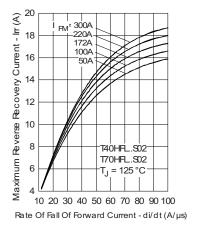
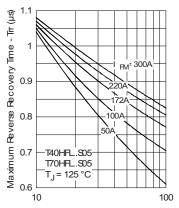


Fig. 21 - Recovery Current Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 22 - Recovery Time Characteristics

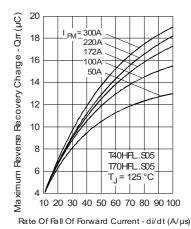
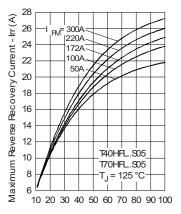
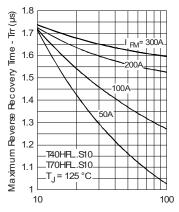


Fig. 23 - Recovery Charge Characteristics



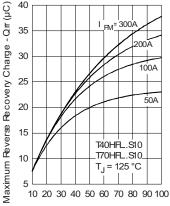
Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 24 - Recovery Current Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

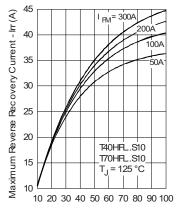
Fig. 25 - Recovery Time Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

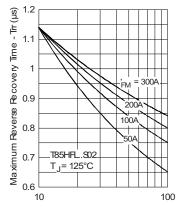
Fig. 26 - Recovery Charge Characteristics

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Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 27 - Recovery Current Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 28 - Recovery Time Characteristics

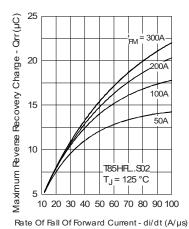
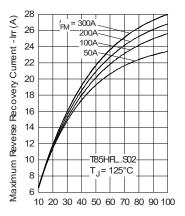
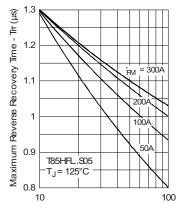


Fig. 29 - Recovery Charge Characteristics



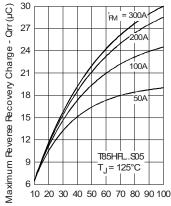
Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 30 - Recovery Current Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

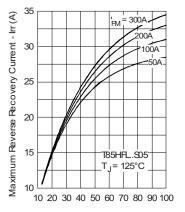
Fig. 31 - Recovery Time Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

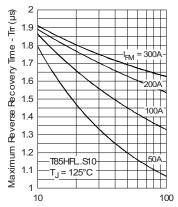
Fig. 32 - Recovery Charge Characteristics

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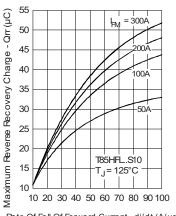
Pate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 33 - Recovery Current Characteristics



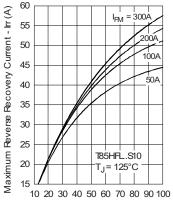
Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 34 - Recovery Time Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 35 - Recovery Charge Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 36 - Recovery Current Characteristics

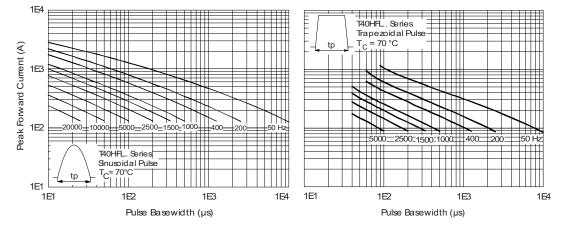


Fig. 37 - Frequency Characteristics

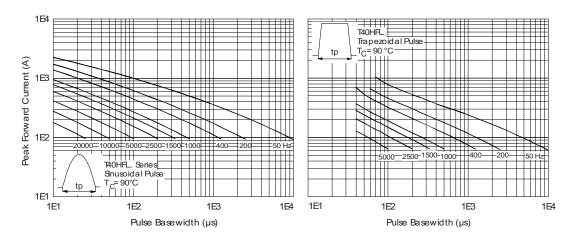


Fig. 38 - Frequency Characteristics

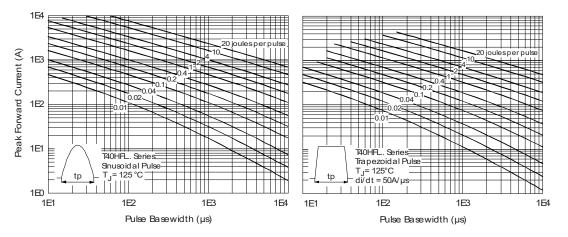


Fig. 39 - Maximum Forward Energy Power Loss Characteristics

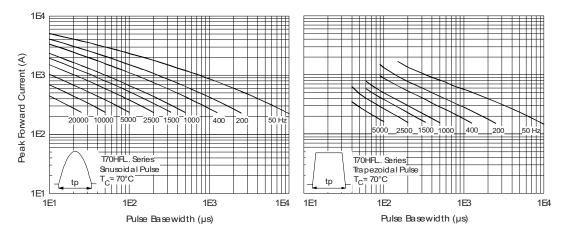


Fig. 40 - Frequency Characteristics

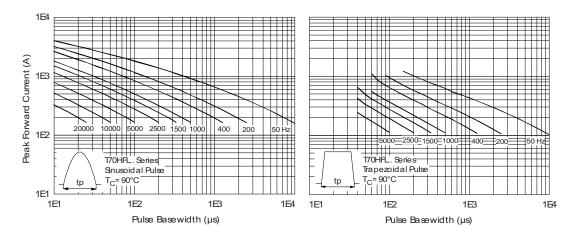


Fig. 41 - Frequency Characteristics

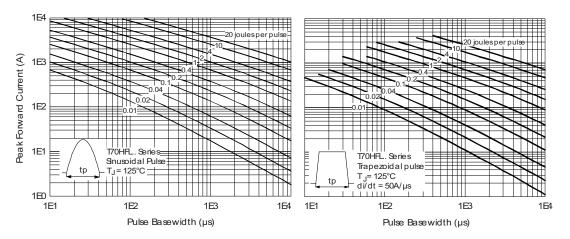


Fig. 42 - Maximum Forward Energy Power Loss Characteristics

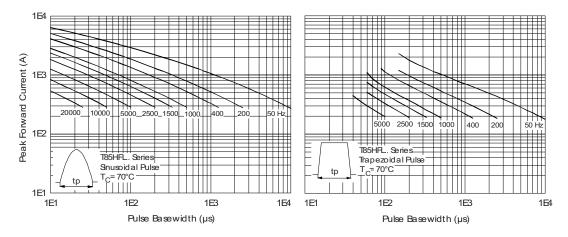


Fig. 43 - Frequency Characteristics

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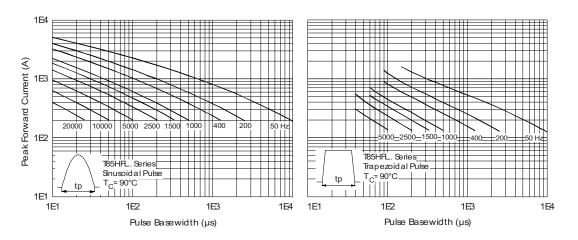


Fig. 44 - Frequency Characteristics

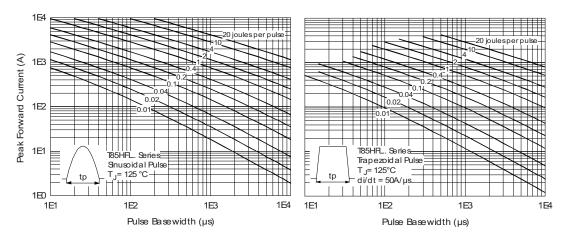


Fig. 45 - Maximum Forward Energy Power Loss Characteristics

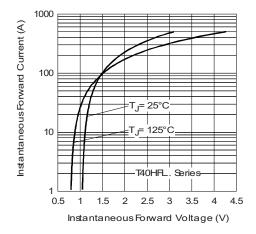


Fig. 46 - Forward Voltage Drop Characteristics

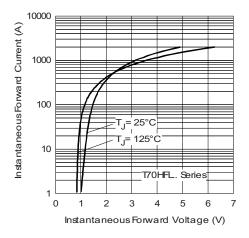


Fig. 47 - Forward Voltage Drop Characteristics

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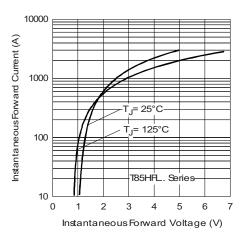


Fig. 48 - Forward Voltage Drop Characteristics

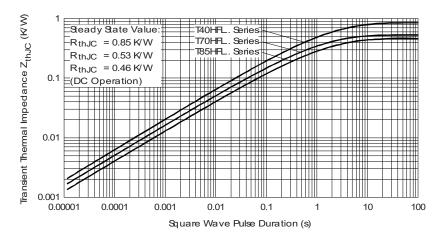
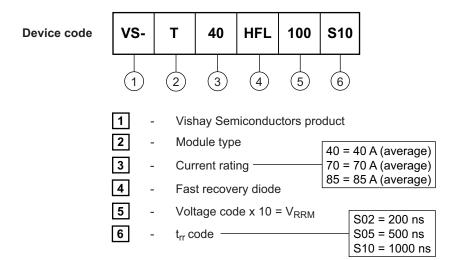


Fig. 49 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE





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CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Single	HFL	20-01				

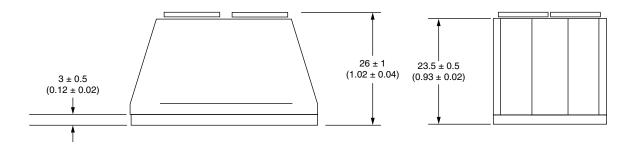
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95313

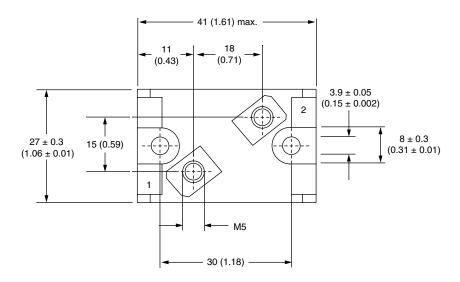


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D-55 T-Module Diode Standard and Fast Recovery

DIMENSIONS in millimeters (inches)





Note

• 1 = Anode 2 = Cathode



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